**CLAIMS**

1. A method of cleaning a substrate comprising:
rotating a substrate disposed on a substrate support;
spraying a front side of the substrate using steam through a front side nozzle assembly;
spraying a back side of the substrate using steam through a back side dispenser assembly; and
dispensing a heated chemical over the front side of the substrate,
wherein dispensing the heated chemical over the front side of the substrate comprises mixing the heated chemical and a nitrogen gas in a chemical heating and dispensing nozzle (POU nozzle), wherein the POU nozzle is movable between a center of the substrate and an outer perimeter of the substrate; and
wherein the POU nozzle comprises:
a first conduit coupled to a heat exchanger, wherein the heat exchanger is coupled to a steam source and a cleaning chemical source, wherein the heat exchanger releases the heated chemical into the first conduit of the POU nozzle; and
a second conduit coupled to a nitrogen gas source.

2. The method of claim 1, wherein spraying the front side of the substrate comprises applying a top spray nozzle above the substrate support.

3. The method of claim 1, wherein spraying the back side of the substrate comprises releasing steam through a center opening of a back plate disposed below the substrate.

4. The method of claim 1, further comprising:
rinsing the top side of the substrate using deionized water (DIW) through the front side nozzle assembly; and
rinsing the back side of the substrate using DIW through the back side dispenser assembly.

5. The method of claim 4, wherein rinsing the back side and the front side of the substrate comprises spraying the back side and the front side with steam and DIW.

6. The method of claim 1, wherein spraying the front side and the back side of the substrate comprises heating the substrate to a temperature between 90°C and 140°C.

7. The method of claim 1, wherein spraying the back side of the substrate comprises releasing steam through a plurality of perforations of a back plate.

8. The method of claim 1, further comprising applying megasonic energy to the substrate, wherein one or more vibrating transducer elements are disposed within a back plate.

9. The method of claim 1, wherein dispensing the heated chemical comprises dispensing 20 mL to 50 mL of chemical to cover the front side of the substrate.

10. The method of claim 1, further comprising drying the substrate by dispensing isopropyl alcohol (IPA) and DIW at a substrate temperature between 25°C and 40°C.

11. The method of claim 1, further comprising:
applying a nitrogen blanket over the front side of the substrate; and
rinsing the front side of the substrate with carbon dioxide dissolved DIW.

12. An apparatus for cleaning a substrate comprising:

a chamber having a substrate support and a back plate disposed therein;

a point of use (POU) nozzle disposed above the substrate support, wherein the POU nozzle comprises:

a first conduit coupled to a fluid source; and

a second conduit coupled to a nitrogen source;

a front side nozzle assembly disposed above the substrate support, wherein the front side nozzle assembly is coupled to a first steam source and a first deionized water (DIW) source; and

a back side dispenser assembly disposed below the substrate support, wherein the back side dispenser assembly is coupled to a second steam source and a second DIW source.

13. The apparatus of claim 12, wherein the back plate comprises a center opening, wherein the center opening is in fluid communication with an orifice of the back side dispenser assembly.

14. The apparatus of claim 12, wherein the back plate comprises a plurality of apertures, wherein each of the plurality of apertures are in fluid communication with an orifice of the back side dispenser assembly.

15. The apparatus of claim 12, wherein the back plate comprises one or more vibrating transducer elements.

16. The apparatus of claim 12, wherein the first conduit of the POU nozzle is coupled to a heat exchanger, wherein the heat exchanger comprises steam configured to heat a cleaning fluid from the fluid source.

17. The apparatus of claim 12, wherein the POU nozzle is movable between a center of the back plate and an outer perimeter of the back plate.

18. The apparatus of claim 12, wherein the front side nozzle assembly is configured to heat a front side of the substrate using the steam.

19. A method of processing a substrate comprising:

polishing the substrate using a chemical mechanical planarization (CMP) process;

rotating the substrate disposed on a substrate support;

heating a front side of the substrate using steam through a front side nozzle assembly;

heating a back side of the substrate using steam through a back side dispenser assembly;

dispensing a heated chemical over the front side of the substrate;

rinsing the front side and the back side of the substrate using carbon dioxide dissolved DIW and steam; and

drying the substrate, wherein drying the substrate comprises flowing a nitrogen gas and drying fluid over the front side of the substrate.

20. An apparatus for cleaning a substrate comprising:

a chamber having a substrate support and a back plate disposed therein;

a point of use (POU) nozzle disposed over the substrate support, wherein the POU nozzle is movable between:

a center of the back plate; and

an outer perimeter of the back plate;

a front side nozzle assembly disposed over a surface of the substrate support at an off center position relative to a center of the substrate support, wherein the front side nozzle assembly is coupled to:

a first steam source; and

a first deionized water (DIW) source; and

a back side dispenser assembly positioned to dispense a fluid to a back side of the substrate when the substrate is disposed on the surface of the substrate support, wherein the back side dispenser assembly is coupled to:

the first steam source or a second steam source; and

the first DIW source or a second DIW source.

21. The apparatus of claim 20, wherein the POU nozzle comprises a first conduit coupled to a fluid source and a second conduit coupled to a nitrogen source.

22. The apparatus of claim 21, wherein the first conduit is coupled to a heat exchanger capable of heating fluid provided from the fluid source.

23. The apparatus of claim 20, wherein the POU nozzle is an atomizer.

24. The apparatus of claim 20, wherein the back plate comprises a transducer, wherein the transducer is configured to apply megasonic energy to the fluid being dispensed to the back side of the substrate when the substrate is disposed on the substrate support.

25. The apparatus of claim 20, wherein a piezoelectric transducer is coupled to the back side dispenser assembly and configured to operate at a frequency of 20 kHz to 2 MHz.

26. An apparatus for cleaning a substrate comprising:

a chamber having a substrate support and a back plate disposed therein;

an atomizer disposed over the substrate support, the atomizer capable of dispensing atomized fluid over a front side of the substrate support;

a front side nozzle assembly disposed over the substrate support at an off center position relative to a center of the substrate support, the front side nozzle assembly configured to dispense a fluid over the front side of the substrate support; and

a back side dispenser assembly positioned to dispense a fluid to a back side of a substrate when the substrate is disposed on the surface of the substrate support, the back side dispenser assembly comprising a back plate comprising a plurality of apertures, the plurality of apertures in fluid communication with the back side of the substrate when the substrate is disposed on the surface of the substrate support.

27. The apparatus of claim 26, wherein the back side dispenser assembly comprises a plurality of nozzles capable of dispensing steam and deionized water simultaneously.

28. The apparatus of claim 26, wherein the back plate further comprises megasonic elements.

29. The apparatus of claim 26, wherein the back plate is vertically movable.

30. The apparatus of claim 26, wherein the front side nozzle assembly is capable of moving over the surface of the substrate between a center of the substrate support and an edge of the substrate when a substrate is present during processing.

31. The apparatus of claim 26, wherein the front side nozzle assembly is capable of dispensing DIW at a flow rate of 800 mL/min to 2000 mL/min.